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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DDR, PCIe, SERDES
Connectivity	CANbus, Ethernet, I ² C, SPI, UART/USART, USB
Speed	166MHz
Primary Attributes	FPGA - 60K Logic Modules
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m2s060t-1fg484m

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Table 15 • Timing Model Parameters

Index	Parameter	Description	Speed Grade -1	Units	Notes
A	t_{PY}	Propagation Delay of DDR3 Receiver	1.672	ns	Refer to page 52 for more information
B	t_{CLKQ}	Clock-to-Q of the Input Data Register	0.165	ns	Refer to page 67 for more information
	t_{SUD}	Setup Time of the Input Data Register	0.369	ns	Refer to page 67 for more information
C	t_{RCKH}	Input High Delay for Global Clock	1.55	ns	Refer to page 78 for more information
	t_{RCKL}	Input Low Delay for Global Clock	0.861	ns	Refer to page 78 for more information
D	t_{PY}	Input Propagation Delay of LVDS Receiver	3.061	ns	Refer to page 58 for more information
E	t_{DP}	Propagation Delay of a three input AND Gate	0.217	ns	Refer to page 76 for more information
F	t_{DP}	Propagation Delay of a OR Gate	0.17	ns	Refer to page 76 for more information
G	t_{DP}	Propagation Delay of a LVDS Transmitter	2.299	ns	Refer to page 58 for more information
H	t_{DP}	Propagation Delay of a three input XOR Gate	0.236	ns	Refer to page 76 for more information
I	t_{DP}	Propagation Delay of LVCMOS 2.5 V Transmitter, Drive strength of 16mA on the MSIO Bank	2.717	ns	Refer to page 31 for more information
J	t_{DP}	Propagation Delay of a two input NAND Gate	0.17	ns	Refer to page 76 for more information
K	t_{DP}	Propagation Delay of LVCMOS 2.5 V Transmitter, Drive strength of 8mA on the MSIO Bank	2.594	ns	Refer to page 31 for more information
L	t_{CLKQ}	Clock-to-Q of the Data Register	0.112	ns	Refer to page 67 for more information
	t_{SUD}	Setup Time of the Data Register	0.262	ns	Refer to page 67 for more information
M	t_{DP}	Propagation Delay of a two input AND gate	0.17	ns	Refer to page 76 for more information
N	t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.272	ns	Refer to page 69 for more information
	t_{OSUD}	Setup Time of the Output Data Register	0.196	ns	Refer to page 69 for more information

Table 15 • Timing Model Parameters (continued)

Index	Parameter	Description	Speed Grade -1	Units	Notes
O	t_{DP}	Propagation Delay of SSTL2, Class I Transmitter on the MSIO Bank	2.283	ns	Refer to page 47 for more information
P	t_{DP}	Propagation Delay of LVCMOS 1.5 V Transmitter, Drive strength of 12mA, fast slew on the DDRIO Bank	3.703	ns	Refer to page 38 for more information

8. User I/O Characteristics

There are three types of I/Os supported in the IGLOO2 FPGA and SmartFusion2 SoC FPGA families: MSIO, MSIOD, and DDRIO I/O banks. The I/O standards supported by the different I/O banks is described in the “I/Os” section of the *UG0445: IGLOO2 FPGA and SmartFusion2 SoC FPGA Fabric User Guide*.

8.1 Input Buffer and AC Loading

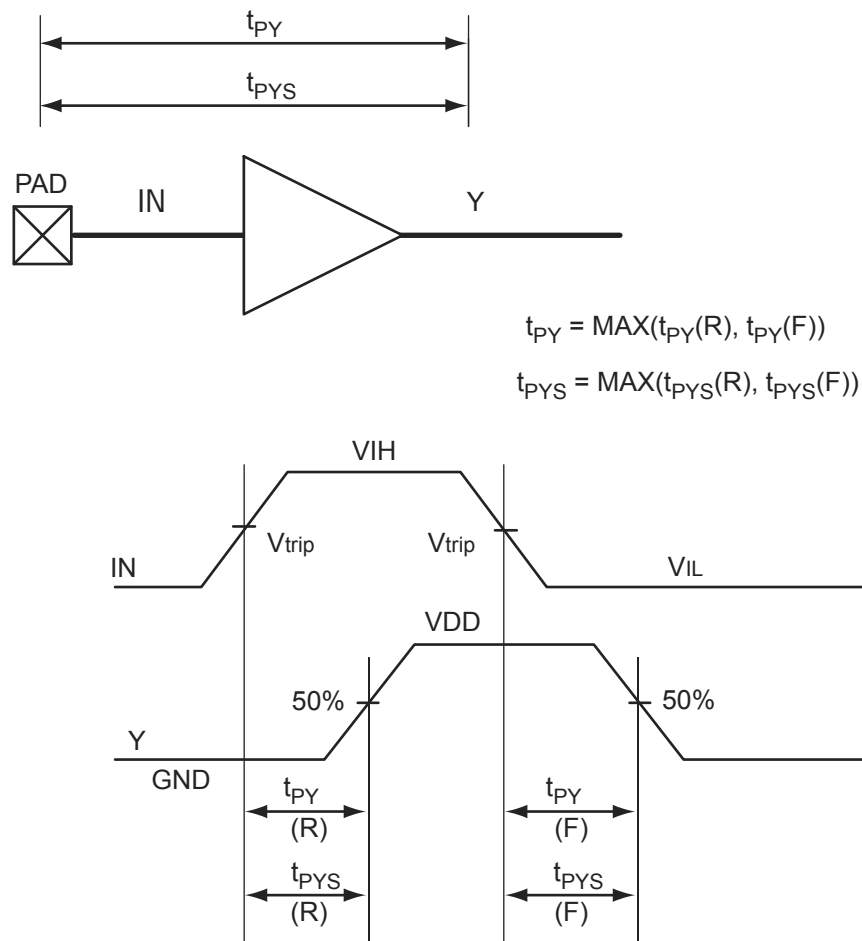


Figure 2 • Input Buffer AC Loading

8.6.5.2. AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 44 • LVCMOS 1.5 V AC Switching Characteristics for Receiver (Input Buffers)

 Worst-Case Military Conditions: $T_J=125^{\circ}\text{C}$, $V_{DD}=1.14\text{ V}$, $V_{DDI}=1.425\text{ V}$

	ODT (On Die Termination)	Speed Grade -1		Units
		t_{PY}	t_{PYS}	
LVCMOS 1.5 V (for DDRIO I/O Bank with Fixed Codes)	none	2.19	2.216	ns
LVCMOS 1.5 V (for MSIO I/O Bank)	none	3.679	3.652	ns
	50	4.151	4.126	ns
	75	3.984	3.953	ns
	150	3.823	3.791	ns
LVCMOS 1.5 V (for MSIOD I/O Bank)	none	3.262	3.229	ns
	50	3.76	3.739	ns
	75	3.555	3.52	ns
	150	3.395	3.359	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 45 • LVCMOS 1.5 V AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

 Worst-Case Military Conditions: $T_J=125^{\circ}\text{C}$, $V_{DD}=1.14\text{ V}$, $V_{DDI}=1.425\text{ V}$

Output Drive Selection	Slew Control	Speed Grade -1					Units
		t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LVCMOS 1.5 V (for DDRIO I/O Bank with Fixed Codes)							
2 mA	slow	5.712	4.796	5.735	5.814	5.138	ns
	medium	5.094	4.274	5.114	5.484	4.779	ns
	medium_fast	4.793	4.013	4.81	5.288	4.625	ns
	fast	4.762	3.98	4.78	5.261	4.615	ns
4 mA	slow	4.966	4.133	4.956	6.763	6.05	ns
	medium	4.412	3.62	4.401	6.433	5.664	ns
	medium_fast	4.145	3.358	4.131	6.249	5.507	ns
	fast	4.116	3.338	4.103	6.238	5.498	ns
6 mA	slow	4.744	3.869	4.728	7.173	6.383	ns
	medium	4.212	3.382	4.195	6.837	6.004	ns
	medium_fast	3.951	3.135	3.93	6.668	5.861	ns
	fast	3.919	3.11	3.899	6.644	5.845	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)
Table 59 • HSTL 15 AC Switching Characteristics for Transmitter (Output and Tristate Buffers)
 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 1.425\text{ V}$

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
HSTL Class I (for DDRIO I/O Bank)						
Single Ended	2.922	2.91	2.904	3.225	3.218	ns
Differential	2.907	2.757	2.755	2.662	2.66	ns
HSTL Class II (for DDRIO I/O Bank)						
Single Ended	2.817	2.735	2.735	2.644	2.644	ns
Differential	2.827	2.81	2.803	3.205	3.197	ns

8.7.2 Stub-Series Terminated Logic

Stub-Series Terminated Logic (SSTL) for 2.5 V (SSTL2), 1.8 V (SSTL18), and 1.5 V (SSTL15) is supported in IGLOO2 and SmartFusion2 SoC FPGAs. SSTL2 is defined by JEDEC standard JESD8-9B and SSTL18 is defined by JEDEC standard JESD8-15. IGLOO2 SSTL I/O configurations are designed to meet double data rate standards DDR/2/3 for general purpose memory buses. Double data rate standards are designed to meet their JEDEC specifications as defined by JEDEC standard JESD79F for DDR, JEDEC standard JESD79-2F for DDR, JEDEC standard JESD79-3D for DDR3, and JEDEC standard JESD209A for LPDDR.

8.7.3 Stub-Series Terminated Logic 2.5 V (SSTL2)

SSTL2 Class I and Class II are supported in IGLOO2 and SmartFusion2 SoC FPGAs and also comply with reduced and full drive of double data rate (DDR) standards. IGLOO2 and SmartFusion2 SoC FPGA I/Os supports both standards for single-ended signaling and differential signaling for SSTL2. This standard requires a differential amplifier input buffer and a push-pull output buffer.

8.7.3.1 Minimum and Maximum DC Input and Output Levels Specification
Table 60 • DDR1/SSTL2 Minimum and Maximum DC Input and Output Levels

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Recommended DC Operating Conditions						
VDDI	Supply voltage		2.375	2.5	2.625	V
VTT	Termination voltage		1.164	1.250	1.339	V
VREF	Input reference voltage		1.164	1.250	1.339	V
SSTL2 DC Input Voltage Specification						
VIH (DC)	DC input logic High		$V_{REF} + 0.15$	–	2.625	V
VIL (DC)	DC input logic Low		–0.3	–	$V_{REF} - 0.15$	V
IIH (DC)	Input current High		–	–	10	μA
IIL (DC)	Input current Low		–	–	10	μA
SSTL2 DC Output Voltage Specification						
SSTL2 Class I (DDR Reduced Drive)						
VOH	DC output logic High		$V_{TT} + 0.608$	–	–	V
VOL	DC output logic Low		–	–	$V_{TT} - 0.608$	V
IOH at VOH	Output minimum source DC current		8.1	–	–	mA

Table 63 • DDR1/SSTL2 AC Switching Characteristics for Transmitter (Output and Tristate Buffers)
Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 2.375\text{ V}$ (continued)

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
MSIO I/O Bank						
Single Ended	2.563	2.208	2.19	2.205	2.187	ns
Differential	2.703	2.566	2.555	2.363	2.353	ns

8.7.4 Stub-Series Terminated Logic 1.8 V (SSTL18)

SSTL18 Class I and Class II are supported in IGLOO2 and SmartFusion2 SoC FPGAs, and also comply with the reduced and full drive double data rate (DDR2) standard. IGLOO2 and SmartFusion2 SoC FPGA I/Os support both standards for single-ended signaling and differential signaling for SSTL18. This standard requires a differential amplifier input buffer and a push-pull output buffer.

8.7.4.1 Minimum and Maximum Input and Output Levels Specification

Table 64 • DDR2/SSTL18 AC/DC Minimum and Maximum Input and Output Levels Specification

Symbols	Parameters	Conditions	Min	Typ	Max	Units	Notes
Recommended DC Operating Conditions							
VDDI	Supply voltage		1.71	1.8	1.89	V	–
VTT	Termination voltage		0.838	0.900	0.964	V	–
VREF	Input reference voltage		0.838	0.900	0.964	V	–
SSTL18 DC Input Voltage Specification							
VIH (DC)	DC input logic High		$V_{REF} + 0.125$	–	1.89	V	–
VIL (DC)	DC input logic Low		–0.3	–	$V_{REF} - 0.125$	V	–
IIH (DC)	Input current High		–	–	10	μA	–
IIL (DC)	Input current Low		–	–	10	μA	–
SSTL18 DC Output Voltage Specification							
SSTL18 Class I (DDR2 Reduced Drive)							
VOH	DC output logic High		$V_{TT} + 0.603$	–	–	V	–
VOL	DC output logic Low		–	–	$V_{TT} - 0.603$	V	–
IOH at VOH	Output minimum source DC current (DDRIO I/O Bank only)		6.0	–	–	mA	–
IOL at VOL	Output minimum sink current (DDRIO I/O Bank only)		–6.0	–	–	mA	–
SSTL18 Class II (DDR2 Full Drive)							
VOH	DC output logic High		$V_{TT} + 0.603$	–	–	V	–
VOL	DC output logic Low		–	–	$V_{TT} - 0.603$	V	–
IOH at VOH	Output minimum source DC current (DDRIO I/O Bank only)		12.0	–	–	mA	–
Note: *To meet JEDEC Electrical Compliance, use DDR2 Full Drive Transmitter.							*

8.7.6.2 AC Switching Characteristics

Table 75 • LPDDR AC Switching Characteristics for Receiver (Input Buffers)
Worst-Case Military Conditions: $T_j=125^{\circ}\text{C}$, $V_{DD}=1.14\text{ V}$, $V_{DDI}=1.71\text{ V}$

	ODT (On Die Termination)	Speed Grade -1	Units
		t_{PY}	
LPDDR (for DDRIO I/O Bank with Fixed Codes)			
Pseudo-Differential	None	1.633	ns
True-Differential	None	1.65	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 76 • LPDDR AC Switching Characteristics for Transmitter (Output and Tristate Buffers)
Worst-Case Military Conditions: $T_j=125^{\circ}\text{C}$, $V_{DD}=1.14\text{ V}$, $V_{DDI}=1.71\text{ V}$

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LPDDR Reduced Drive (for DDRIO I/O Bank)						
Single Ended	2.645	2.431	2.434	2.396	2.398	ns
Differential	2.652	3.044	3.038	2.46	2.455	ns
LPDDR Full Drive (for DDRIO I/O Bank)						
Single Ended	2.532	2.401	2.398	2.368	2.365	ns
Differential	2.546	2.509	2.503	2.852	2.845	ns

8.7.6.3 Minimum and Maximum AC/DC Input and Output Levels Specification using LPDDR-LVCMOS 1.8 V Mode

Table 77 • LPDDR-LVCMOS 1.8 V Mode, Minimum and Maximum DC Input and Output Levels
(Applicable to DDRIO I/O Bank Only)

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LPDDR-LVCMOS 1.8 V Recommended DC Operating Conditions						
V _{DDI}	Supply Voltage	–	1.710	1.8	1.89	V
LPDDR-LVCMOS 1.8 V Mode DC Input Voltage Specification						
V _{IH} (DC)	DC input Logic HIGH for (MSIOD and DDRIO I/O Banks)	–	0.65 x V _{DDI}	–	1.89	V
V _{IH} (DC)	DC input Logic HIGH (for MSIO I/O Bank)	–	0.65 x V _{DDI}	–	3.45	V
V _{IL} (DC)	DC input Logic LOW	–	-0.3	–	0.35 x V _{DDI}	V
I _{IH} (DC)	Input current HIGH	–	–	–	10	μA
I _{IL} (DC)	Input current LOW	–	–	–	10	μA
LPDDR-LVCMOS 1.8 V Mode DC Output Voltage Specification						
V _{OH}	DC output Logic HIGH	–	V _{DDI} - 0.45	–	–	V
V _{OL}	DC output Logic LOW	–	–	–	0.45	V

8.8.1.2 LVDS25 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 85 • LVDS25 Receiver Characteristics

 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 2.375\text{ V}$

	On-Die Termination (ODT)	Speed Grade -1	Units
		t_{PY}	
LVDS (for MSIO I/O Bank)	None	3.061	ns
	100	3.057	ns
LVDS (for MSIOD I/O Bank)	None	2.792	ns
	100	2.787	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 86 • LVDS25 Transmitter Characteristics

 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 2.375\text{ V}$

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LVDS (for MSIO I/O Bank)	2.299	2.602	2.589	2.305	2.32	ns
LVDS (for MSIOD I/O Bank)						
No pre-emphasis	1.656	1.845	1.838	1.992	1.969	ns
Min pre-emphasis	1.583	1.868	1.866	2.018	1.998	ns
Med pre-emphasis	1.559	1.893	1.886	2.045	2.021	ns

8.8.1.3 LVDS33 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 87 • LVDS33 Receiver Characteristics

 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 3.15\text{ V}$

	On Die Termination (ODT)	Speed Grade -1	Units
		t_{PY}	
LVDS33 (for MSIO I/O Bank)	None	2.763	ns
	100	2.76	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 88 • LVDS33 Transmitter Characteristics

 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 3.15\text{ V}$

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LVDS33 (for MSIO I/O Bank)	2.069	2.112	2.106	2.078	2.09	ns

8.8.5.2. AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 103 • RSDS AC Switching Characteristics for Receiver (Input Buffers)

Worst-case Military conditions: $T_J = 125^{\circ}\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 2.375\text{ V}$

	On-Die Termination (ODT)	Speed Grade -1	Units
		t_{PY}	
RSDS (for MSIO I/O Bank)	None	3.112	ns
	100	3.108	ns
RSDS (for MSIOD I/O Bank)	None	2.832	ns
	100	2.821	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 104 • RSDS AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Worst-case Military conditions: $T_J = 125^{\circ}\text{C}$, $V_{DD} = 1.14\text{ V}$, $V_{DDI} = 2.375\text{ V}$

	Speed Grade -1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
RSDS (for MSIO I/O Bank)	2.256	2.484	2.472	2.111	2.096	ns
RSDS (for MSIOD I/O Bank)						
No pre-emphasis	1.661	1.648	1.645	1.675	1.665	ns
Min pre-emphasis	1.651	1.84	1.833	1.988	1.964	ns
Med pre-emphasis	1.577	1.868	1.859	2.019	1.993	ns
Max pre-emphasis	1.555	1.894	1.883	2.047	2.018	ns

8.8.6 LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Similar to LVDS, two pins are needed. It also requires external resistor termination. IGLOO2 and SmartFusion2 SoC FPGAs support only LVPECL receivers and do not support LVPECL transmitters.

8.8.6.1 Minimum and Maximum Input and Output Levels

Table 105 • LVPECL DC Voltage Specification (Applicable to MSIO I/O Banks Only)

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Recommended DC Operating Conditions						
VDDI	Supply voltage		3.15	3.3	3.45	V
LVPECL DC Input Voltage Specification						
VI	DC input voltage		0	–	3.45	V
LVPECL Differential Voltage Specification						
VICM	Input common mode voltage		0.3		2.8	V
VIDIFF	Input differential voltage		100	300	1,000	mV

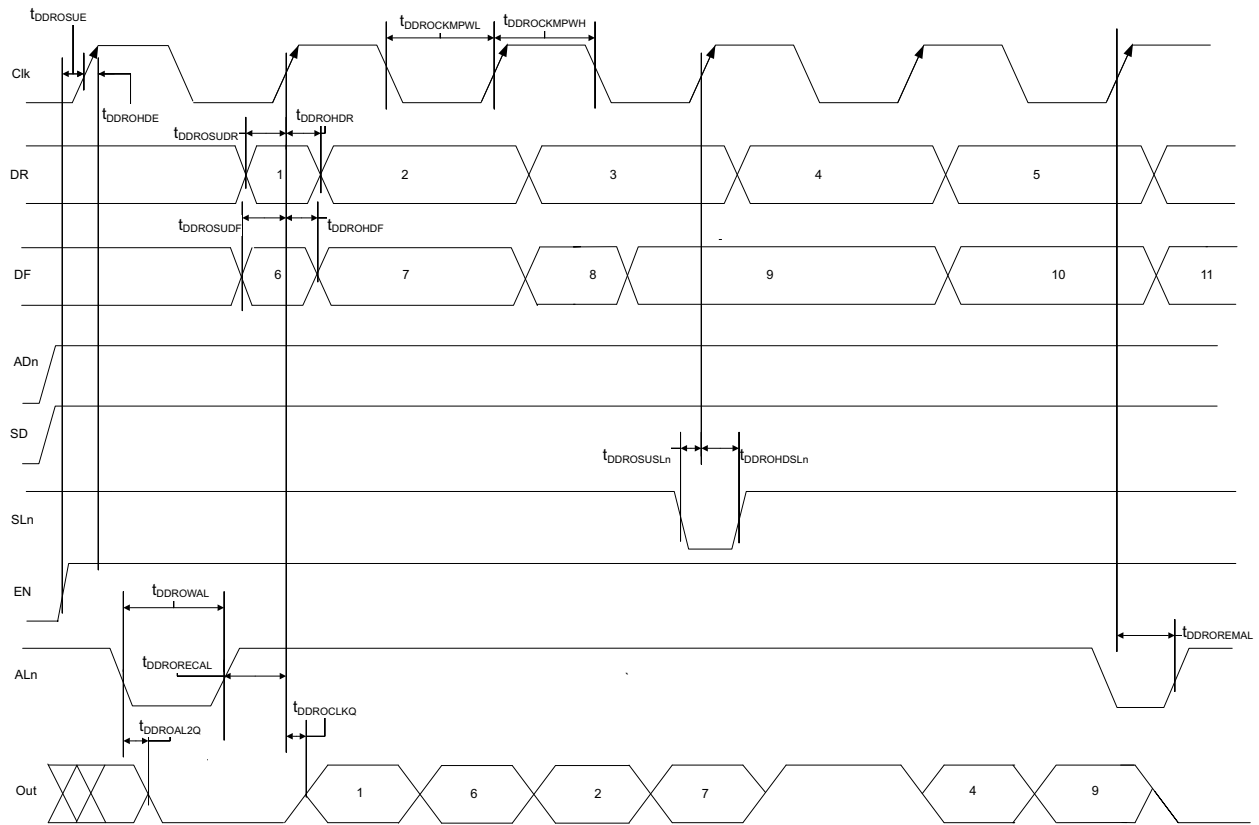


Figure 12 • Output DDR Timing Diagram

9. Logic Element Specifications

9.1 4-input LUT (LUT-4)

The IGLOO2 and SmartFusion2 SoC FPGAs offer a fully permutable 4-input LUT. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *SmartFusion2 and IGLOO2 Macro Library Guide*.

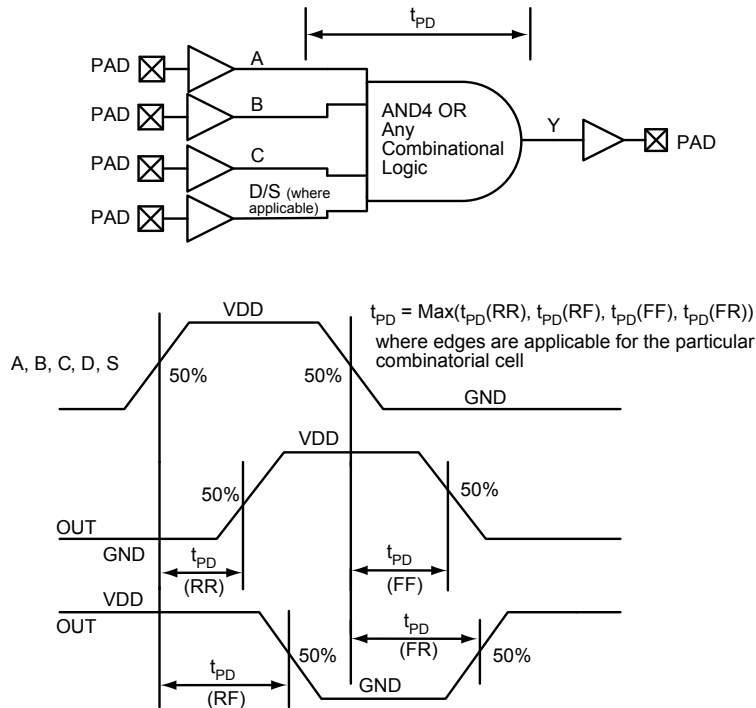


Figure 13 • LUT-4

Timing Characteristics

Table 112 • Combinatorial Cell Propagation Delays
Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$

Combinatorial Cell	Equation	Parameter	Speed Grade -1	Units
INV	$Y = !A$	t_{PD}	0.106	ns
AND2	$Y = A \cdot B$	t_{PD}	0.17	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	0.157	ns
OR2	$Y = A + B$	t_{PD}	0.17	ns
NOR2	$Y = !(A + B)$	t_{PD}	0.157	ns
XOR2	$Y = A \oplus B$	t_{PD}	0.17	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	0.236	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	0.217	ns
AND4	$Y = A \cdot B \cdot C \cdot D$	t_{PD}	0.384	ns

9.2 Sequential Module

IGLOO2 and SmartFusion2 SoC FPGAs offer a separate flip-flop which can be used independently from the LUT. The flip-flop can be configured as a register or a latch and has a data input and optional enable, synchronous load (clear or preset), and asynchronous load (clear or preset).

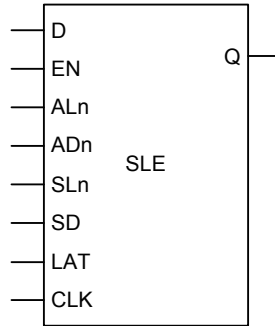


Figure 14 • Sequential Module

Figure 15 shows a configuration with SD = 0 (synchronous clear) and ADn = 1 (asynchronous clear) for a flip-flop (LAT = 0).

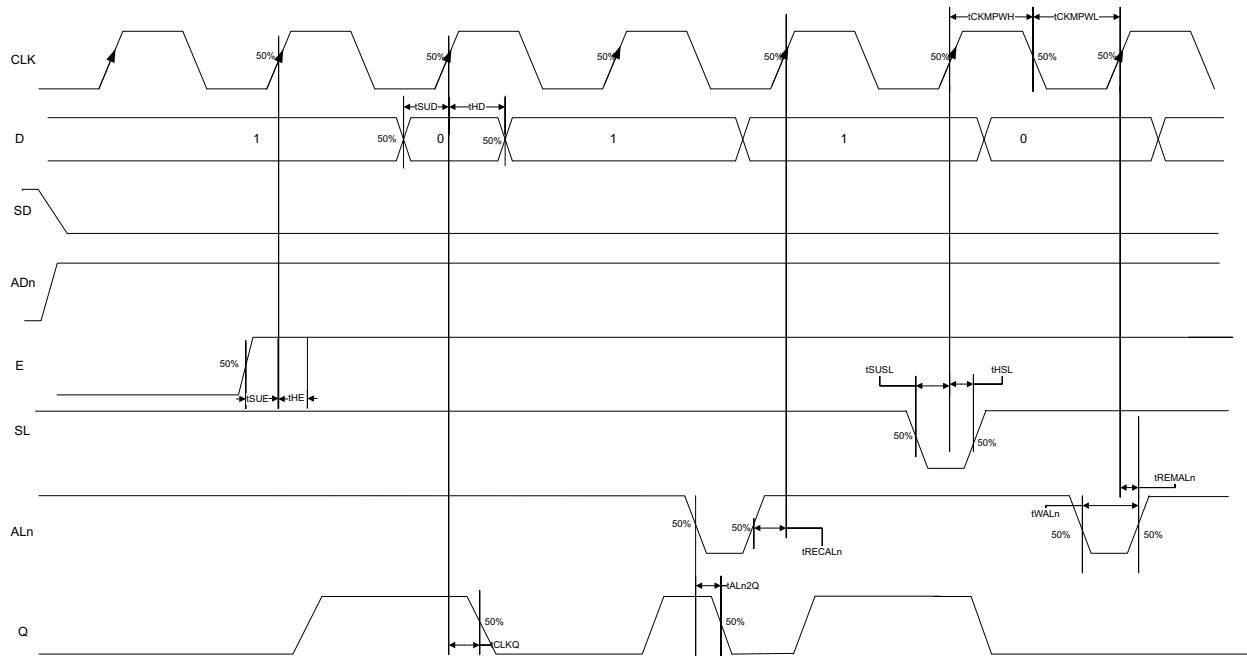


Figure 15 • Sequential Module Timing Diagram

Table 127 • uSRAM (RAM128x9) in 128x9 Mode
 Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V (continued)

Parameter	Description	Speed Grade -1		Units
		Min	Max	
tclkmpwl	Read Clock Minimum pulse Width Low	1.8	–	ns
tpicy	Read Pipe-line clock period	4	–	ns
tplckmpwh	Read Pipe-line clock Minimum Pulse Width High	1.8	–	ns
tplckmpwl	Read Pipe-line clock Minimum Pulse Width Low	1.8	–	ns
tclk2q	Read Access Time with Pipeline Register	–	0.276	ns
	Read Access Time without Pipeline Register	–	1.776	ns
taddrsu	Read Address Setup Time in Synchronous Mode	0.311	–	ns
	Read Address Setup Time in Asynchronous Mode	1.959	–	ns
taddrhd	Read Address Hold Time in Synchronous Mode	0.125	–	ns
	Read Address Hold Time in Asynchronous Mode	-0.704	–	ns
trdensu	Read Enable Setup Time	0.287	–	ns
trdenhd	Read Enable Hold Time	0.059	–	ns
tblksu	Read Block Select Setup Time	1.898	–	ns
tblkhd	Read Block Select Hold Time	-0.671	–	ns
tblk2q	Read Block Select to Out Disable Time (when Pipe-Lined Registered is Disabled)	–	2.14	ns
trstrem	Read Asynchronous Reset Removal Time (Pipelined Clock)	-0.15	–	ns
	Read Asynchronous Reset Removal Time (Non-Pipelined Clock)	0.047	–	ns
trstrec	Read Asynchronous Reset Recovery Time (Pipelined Clock)	0.524	–	ns
	Read Asynchronous Reset Recovery Time (Non-Pipelined Clock)	0.244	–	ns
tr2q	Read Asynchronous Reset to Output Propagation Delay (with Pipe-Line Register Enabled)	–	0.865	ns
tsrstsu	Read Synchronous Reset Setup Time	0.279	–	ns
tsrsthd	Read Synchronous Reset Hold Time	0.062	–	ns
tccy	Write Clock Period	4	–	ns
tcclkmpwh	Write Clock Minimum Pulse Width High	1.8	–	ns
tcclkmpwl	Write Clock Minimum Pulse Width Low	1.8	–	ns
tblksu	Write Block Setup Time	0.417	–	ns
tblkchd	Write Block Hold Time	0.007	–	ns
tdincsu	Write Input Data setup Time	0.104	–	ns
tdinchd	Write Input Data hold Time	0.142	–	ns
taddrcsu	Write Address Setup Time	0.091	–	ns

Table 128 • uSRAM (RAM128x8) in 128x8 Mode
 Worst-Case Military Conditions: $T_J = 125^{\circ}\text{C}$, $V_{DD} = 1.14\text{ V}$ (continued)

Parameter	Description	Speed Grade -1		Units
		Min	Max	
tr2q	Read Asynchronous Reset to Output Propagation Delay (With Pipe-Line Register Enabled)	–	0.865	ns
tsrstu	Read Synchronous Reset Setup Time	0.279	–	ns
tsrsthd	Read Synchronous Reset Hold Time	0.062	–	ns
tccy	Write Clock Period	4	–	ns
tcclkmpwh	Write Clock Minimum Pulse Width High	1.8	–	ns
tcclkmpwl	Write Clock Minimum Pulse Width Low	1.8	–	ns
tblkcsu	Write Block Setup Time	0.417	–	ns
tblkchd	Write Block Hold Time	0.007	–	ns
tdincsu	Write Input Data setup Time	0.104	–	ns
tdinchd	Write Input Data hold Time	0.142	–	ns
taddrcsu	Write Address Setup Time	0.091	–	ns
taddrchd	Write Address Hold Time	0.24	–	ns
twecsu	Write Enable Setup Time	0.41	–	ns
twechd	Write Enable Hold Time	-0.027	–	ns
fmax	Maximum Frequency	–	250	MHz

Table 129 • uSRAM (RAM256x4) in 256x4 Mode
 Worst-Case Military Conditions: $T_J = 125^{\circ}\text{C}$, $V_{DD} = 1.14\text{ V}$

Parameter	Description	Speed Grade -1		Units
		Min	Max	
tcy	Read Clock Period	4	–	ns
tclkmpwh	Read Clock Minimum Pulse Width High	1.8	–	ns
tclkmpwl	Read Clock Minimum pulse Width Low	1.8	–	ns
tpcy	Read Pipe-line clock period	4	–	ns
tpclkmpwh	Read Pipe-line clock Minimum Pulse Width High	1.8	–	ns
tpclkmpwl	Read Pipe-line clock Minimum Pulse Width Low	1.8	–	ns
tclk2q	Read Access Time with Pipeline Register	–	0.276	ns
	Read Access Time without Pipeline Register	–	1.812	ns
taddrsu	Read Address Setup Time in Synchronous Mode	0.311	–	ns
	Read Address Setup Time in Asynchronous Mode	1.993	–	ns
taddrhd	Read Address Hold Time in Synchronous Mode	0.125	–	ns
	Read Address Hold Time in Asynchronous Mode	-0.669	–	ns
trdensu	Read Enable Setup Time	0.287	–	ns

13. Crystal Oscillator

Table 134 describes the electrical characteristics of the crystal oscillator in the IGLOO2 FPGA and SmartFusion2 SoC FPGAs.

Table 134 • Electrical Characteristics of the Crystal Oscillator – High Gain Mode (20 MHz)

Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$

Parameter	Description	Min	Typ	Max	Units
FXTAL	Operating frequency	–	20	–	MHz
ACCXTAL	Accuracy	–	–	0.006	%
CYCXTAL	Output duty cycle	–	49-51	47-53	%
JITPERXTAL	Output Period Jitter (peak to peak)	–	200	300	ps
JITCYCXTAL	Output Cycle to Cycle Jitter (peak to peak)	–	200	550	ps
IDYNXTAL	Operating current	–	1.5	–	mA
VIHXTAL	Input logic level High	$0.9 \times V_{PP}$	–	–	V
VILXTAL	Input logic level Low	–	–	$0.1 \times V_{PP}$	V
SUXTAL	Startup time (with regard to stable oscillator output)	–	–	1	ms

Table 135 • Electrical Characteristics of the Crystal Oscillator – Medium Gain Mode (2 MHz)

Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$

Parameter	Description	Min	Typ	Max	Units
FXTAL	Operating frequency	–	2	–	MHz
ACCXTAL	Accuracy	–	–	0.003	%
CYCXTAL	Output duty cycle	–	49–51	47–53	%
JITPERXTAL	Output Period Jitter (peak to peak)	–	1	5	ns
JITCYCXTAL	Output Cycle to Cycle Jitter (peak to peak)	–	1	5	ns
IDYNXTAL	Operating current	–	0.3	–	mA
VIHXTAL	Input logic level High	$0.9 \times V_{PP}$	–	–	V
VILXTAL	Input logic level Low	–	–	$0.1 \times V_{PP}$	V
SUXTAL	Startup time (with regard to stable oscillator output)	–	–	4.5	ms

Table 136 • Electrical Characteristics of the Crystal Oscillator – Low Gain Mode (32 kHz)

Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$

Parameter	Description	Min	Typ	Max	Units
FXTAL	Operating frequency	–	32	–	kHz
ACCXTAL	Accuracy	–	–	0.006	%
CYCXTAL	Output duty cycle	–	49–51	45.5–54.5	%
JITPERXTAL	Output Period Jitter (peak to peak)	–	150	300	ns
JITCYCXTAL	Output Cycle to Cycle Jitter (peak to peak)	–	150	300	ns

Table 155 • HCSL Minimum and Maximum DC Input Levels (Applicable to SERDES REFCLK Only)

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Recommended DC Operating Conditions						
VDDI	Supply Voltage	–	2.375	2.5	2.625	V
HCSL DC Input Voltage Specification						
VI	DC Input voltage	–	0	–	2.625	V
HCSL Differential Voltage Specification						
VICM	Input common mode voltage	–	0.05	–	2.4	V
VIDIFF	Input differential voltage	–	100	–	1100	mV

Table 156 • HCSL Maximum AC Switching Speeds (Applicable to SERDES REFCLK Only)

Symbols	Parameters	Conditions	Min	Typ	Max	Units
HCSL AC Specifications						
Fmax	Maximum Data Rate (for MSIO IO Bank)	–	–	–	350	Mbps
HCSL Impedance Specifications						
Rt	Termination Resistance	–	–	100	–	Ω

24. SmartFusion2 Specifications

24.1 MSS Clock Frequency

Table 157 • Maximum Frequency for MSS Main Clock

 Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Symbol	Description	Speed Grade –1	Units
M3_CLK	Maximum frequency for the MSS Main Clock (FCLK)	133	MHz

24.2 SmartFusion2 Inter-Integrated Circuit (I²C) Characteristics

This section describes the DC and switching of the I²C interface. Unless otherwise noted, all output characteristics given are for a 100 pF load on the pins. For timing parameter definitions, refer to Figure 16 on page 112.

Table 158 • I²C Characteristics

 Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Definition	Conditions	Min	Typ	Max	Units	Notes
VIL	Input low voltage	Refer to the "Single-Ended I/O Standards" section on page 27 for more information. I/O standard used for illustration: MSIO bank– LVTTTL 8 mA low drive.	–0.3	–	0.8	V	–
VIH	Input high voltage	Refer to the "Single-Ended I/O Standards" section on page 27 for more information. I/O standard used for illustration: MSIO bank – LVTTTL 8 mA low drive.	2	–	3.45	V	–

Table 164 • SPI Characteristics

 Worst-Case Military Conditions: $T_J = 125^\circ\text{C}$, $V_{DD} = 1.14\text{ V}$ (continued)

Symbol	Description	Conditions	All Devices/Speed Grades			Unit	Notes
			Min	Typ	Max		
sp3	SPI_[0 1]_CLK minimum pulse width low						
	SPI_[0 1]_CLK = PCLK/2	–	6	–	–	ns	–
	SPI_[0 1]_CLK = PCLK/4	–	12.05	–	–	ns	–
	SPI_[0 1]_CLK = PCLK/8	–	24.1	–	–	ns	–
	SPI_[0 1]_CLK = PCLK/16	–	0.05	–	–	μs	–
	SPI_[0 1]_CLK = PCLK/32	–	0.095	–	–	μs	–
	SPI_[0 1]_CLK = PCLK/64	–	0.195	–	–	μs	–
	SPI_[0 1]_CLK = PCLK/128	–	0.385	–	–	μs	–
sp4	SPI_[0 1]_CLK, SPI_[0 1]_DO, SPI_[0 1]_SS rise time (10%-90%)	I/O Configuration: LVCMOS 2.5 V- 8mA AC Loading: 35pF Test Conditions: Typical Voltage, 25°C	–	2.77	–	ns	1
sp5	SPI_[0 1]_CLK, SPI_[0 1]_DO, SPI_[0 1]_SS fall time (10%-90%)	I/O Configuration: LVCMOS 2.5 V- 8mA AC Loading: 35pF Test Conditions: Typical Voltage, 25°C	–	2.90 6	–	ns	1
SPI Master Configuration							
sp6m	SPI_[0 1]_DO setup time	–	$(\text{SPI}_x_CLK_period/2) - 3.0$	–	–	ns	2
sp7m	SPI_[0 1]_DO hold time	–	$(\text{SPI}_x_CLK_period/2) - 2.5$	–	–	ns	2
sp8m	SPI_[0 1]_DI setup time	–	8	–	–	ns	2
sp9m	SPI_[0 1]_DI hold time	–	2.5	–	–	ns	2
SPI Slave Configuration							
sp6s	SPI_[0 1]_DO setup time	–	$(\text{SPI}_x_CLK_period/2) - 12.0$	–	–	ns	2
sp7s	SPI_[0 1]_DO hold time	–	$(\text{SPI}_x_CLK_period/2) + 3.0$	–	–	ns	2
sp8s	SPI_[0 1]_DI setup time	–	2	–	–	ns	2